

In1233DE

Abstract

Method for fabricating a spacer structure

The invention relates to a method for fabricating a spacer structure, comprising the steps of: forming a gate insulation layer (2) having a gate deposition-inhibiting layer (2A), a gate layer (3) and a covering deposition-inhibiting layer (4) on a semiconductor substrate (1), and patterning the gate layer (3) and the covering deposition-inhibiting layer (4) in order to form gate stacks (G), an insulation layer (6) being deposited selectively using the deposition-inhibiting layers (2A, 4) for the purpose of highly accurate formation of a spacer structure.

Figure 2C